

TOSHIBA GTR Module Silicon N Channel IGBT

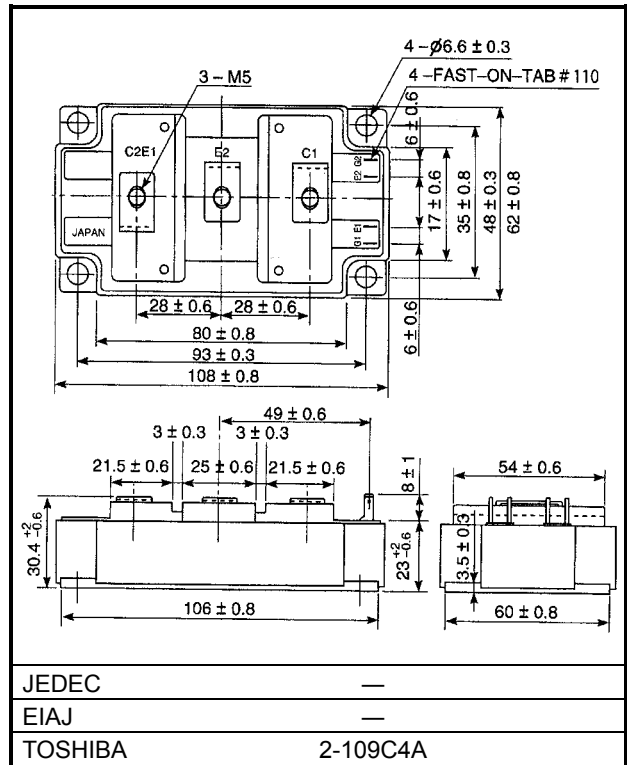
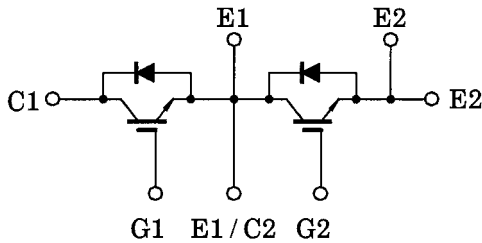
MG150Q2YS51

High Power Switching Applications
 Motor Control Applications

Unit: mm

- High input impedance
- High speed : $t_f = 0.3\mu s$ (Max)
@Inductive Load
- Low saturation voltage
: $V_{CE(sat)} = 3.6V$ (Max)
- Enhancement-mode
- Includes a complete half bridge in one package.
- The electrodes are isolated from case.

Equivalent Circuit



Maximum Ratings (Ta = 25°C)

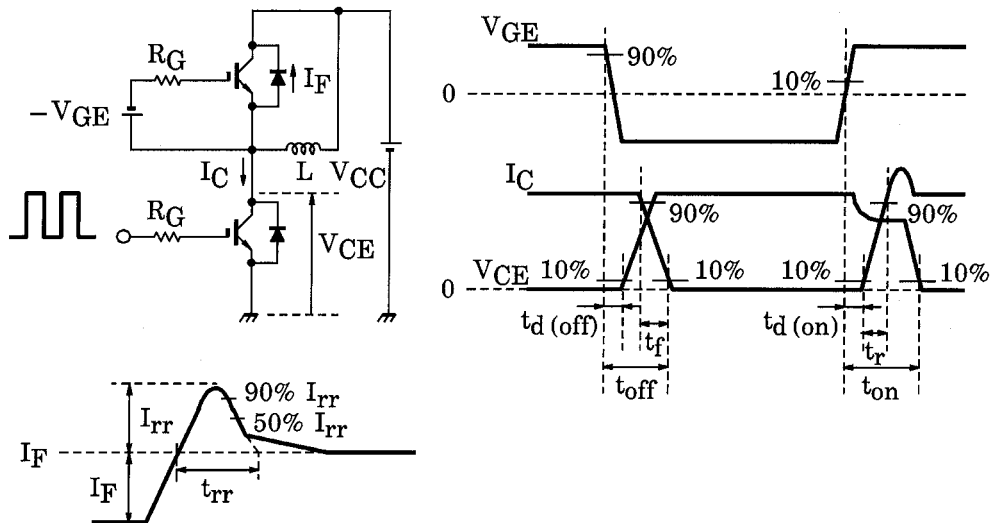
Weight: 430g

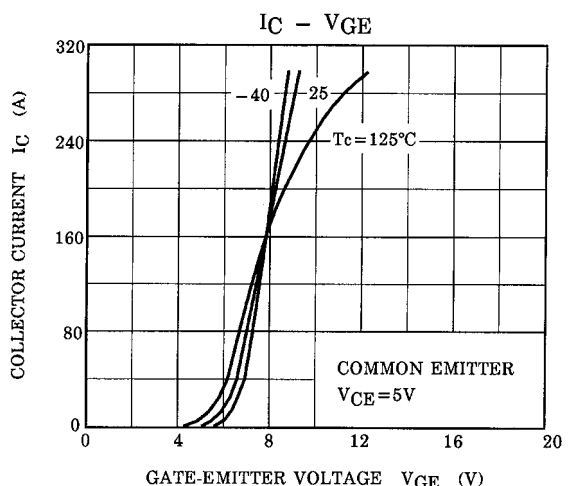
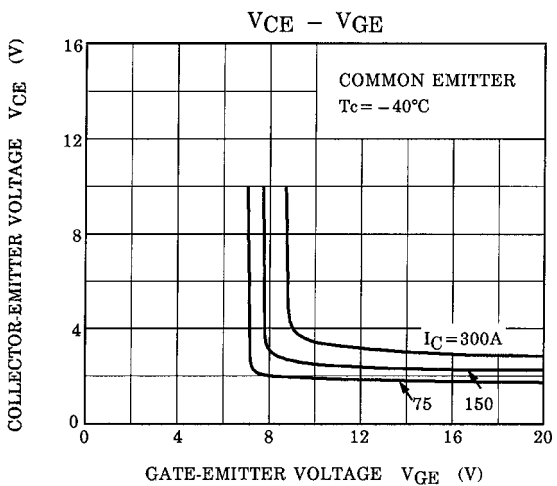
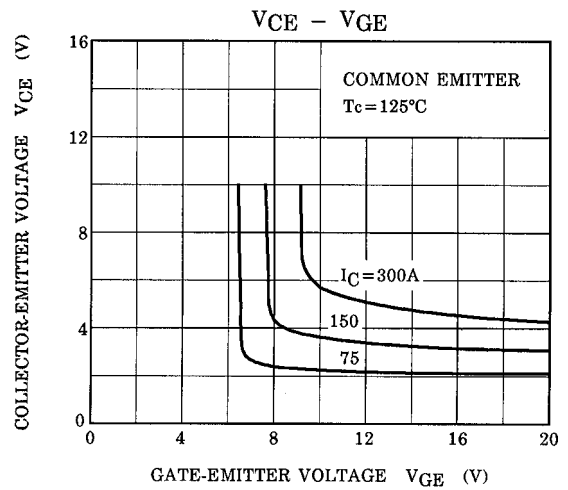
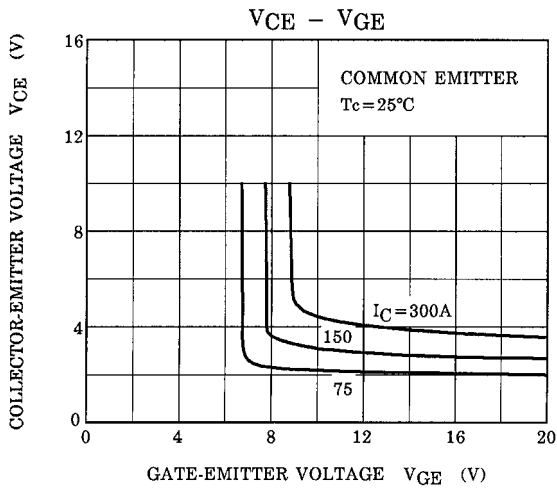
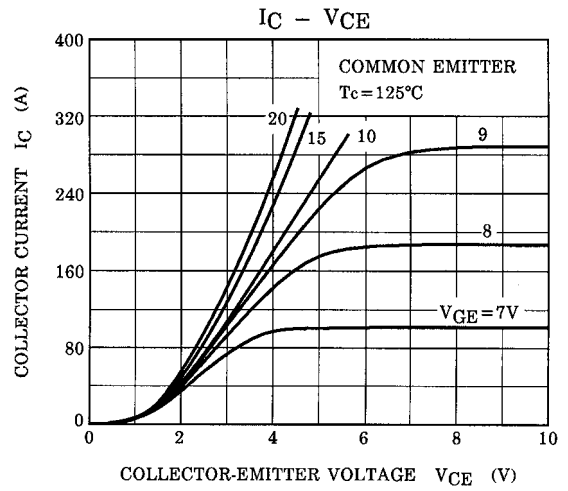
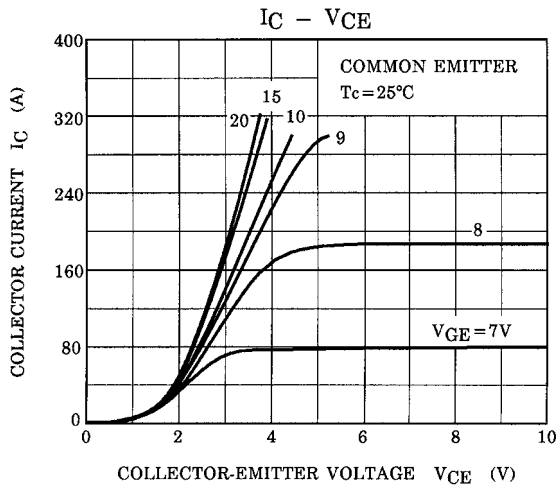
Characteristic	Symbol	Rating	Unit
Collector-emitter voltage	V_{CES}	1200	V
Gate-emitter voltage	V_{GES}	±20	V
Collector current	DC	I_C (25°C / 80°C)	200 / 150
	1ms	I_{CP} (25°C / 80°C)	400 / 300
Forward current	DC	I_F	150
	1ms	I_{FM}	300
Collector power dissipation (Tc = 25°C)	P_C	1250	W
Junction temperature	T_j	150	°C
Storage temperature range	T_{stg}	-40 ~ 125	°C
Isolation voltage	V_{Isol}	2500 (AC 1 min.)	V
Screw torque (Terminal / mounting)	—	3 / 3	N·m

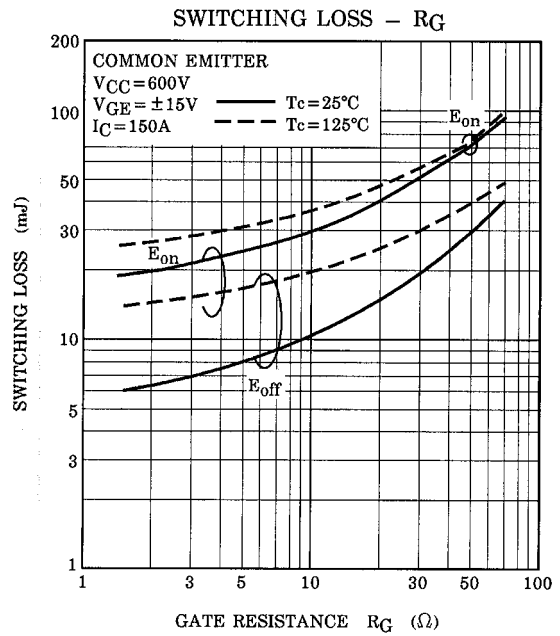
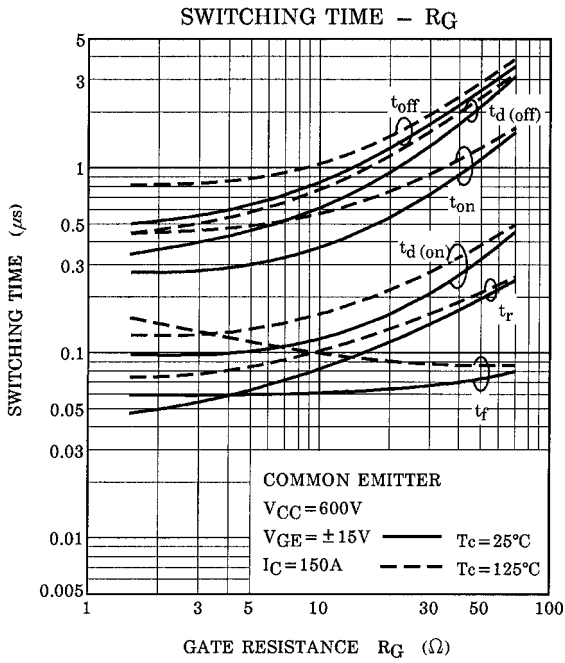
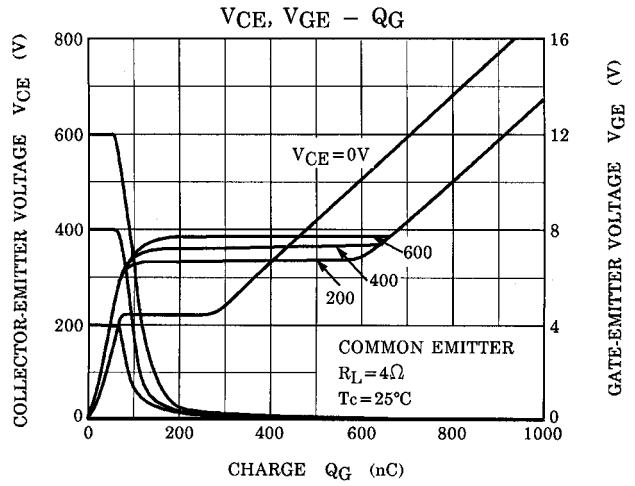
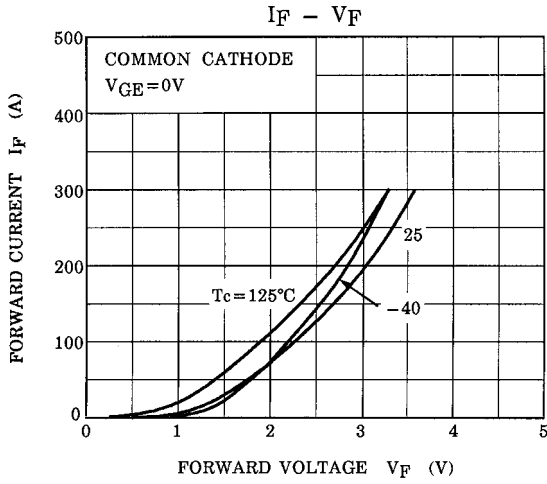
Electrical Characteristics (Ta = 25°C)

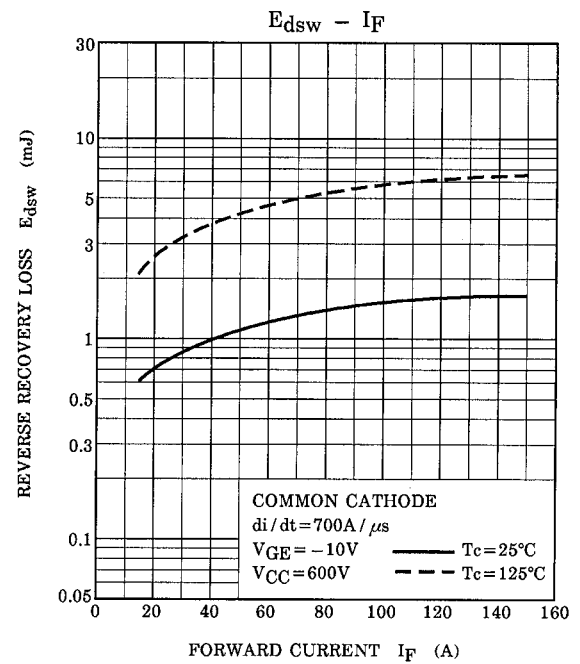
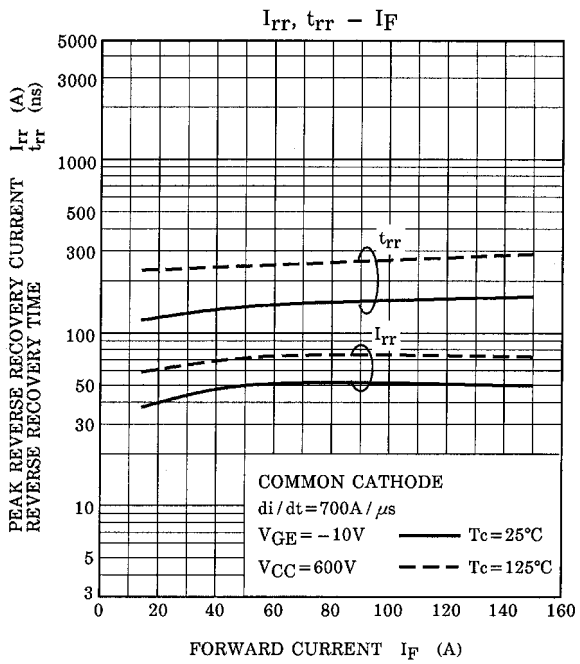
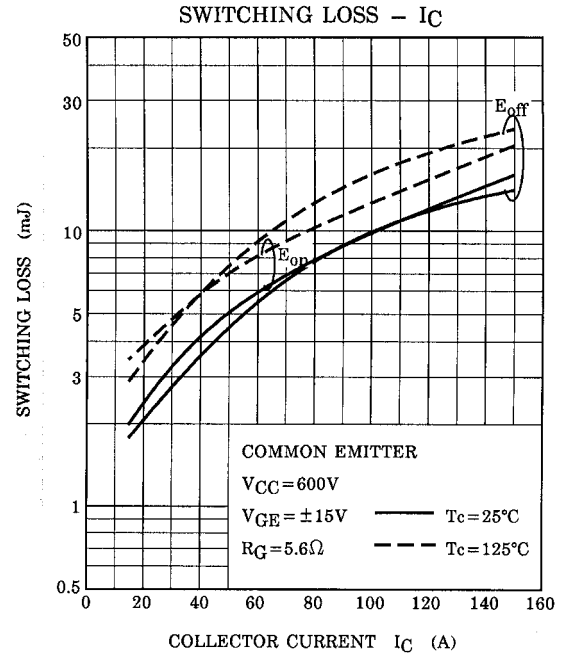
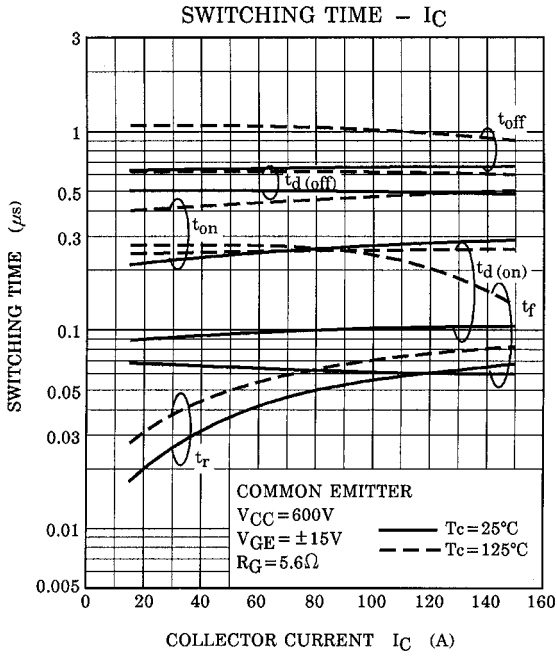
Characteristic	Symbol	Test Condition	Min	Typ.	Max	Unit	
Gate leakage current	I_{GES}	$V_{GE} = \pm 20V, V_{CE} = 0$	—	—	± 500	nA	
Collector cut-off current	I_{CES}	$V_{CE} = 1200V, V_{GE} = 0$	—	—	2.0	mA	
Gate-emitter cut-off voltage	$V_{GE (off)}$	$I_C = 150mA, V_{CE} = 5V$	3.0	—	6.0	V	
Collector-emitter saturation voltage	$V_{CE (sat)}$	$I_C = 150A, V_{GE} = 15V$	$T_j = 25^\circ C$	—	2.8	3.6	V
			$T_j = 125^\circ C$	—	3.1	4.0	
Input capacitance	C_{ies}	$V_{CE} = 10V, V_{GE} = 0, f = 1MHz$	—	18.0	—	nF	
Switching time	Turn-on delay time	$t_{d(on)}$	—	0.05	—	μs	
	Rise time	t_r	—	0.05	—		
	Turn-on time	t_{on}	—	0.2	—		
	Turn-off delay time	$t_{d(off)}$	—	0.5	—		
	Fall time	t_f	—	0.1	0.3		
	Turn-off time	t_{off}	—	0.6	—		
Forward voltage	V_F	$I_F = 150A, V_{GE} = 0$	—	2.4	3.5	V	
Reverse recovery time	t_{rr}	$I_F = 150A, V_{GE} = -10V$ $di/dt = 700A/\mu s$ (Note 1)	—	0.1	0.25	μs	
Thermal resistance	$R_{th (j-c)}$	Transistor stage	—	—	0.1	$^\circ C/W$	
		Diode stage	—	—	0.24		

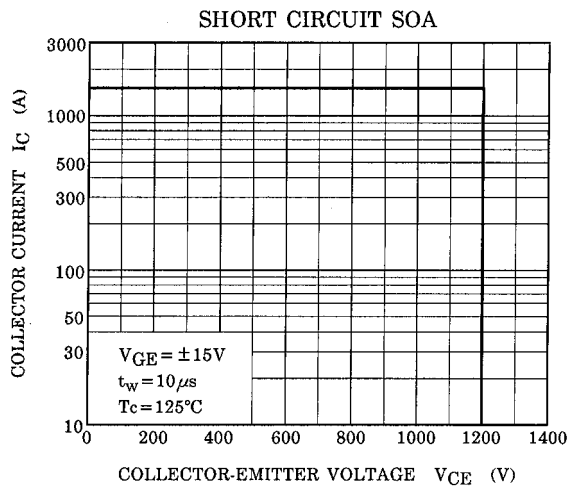
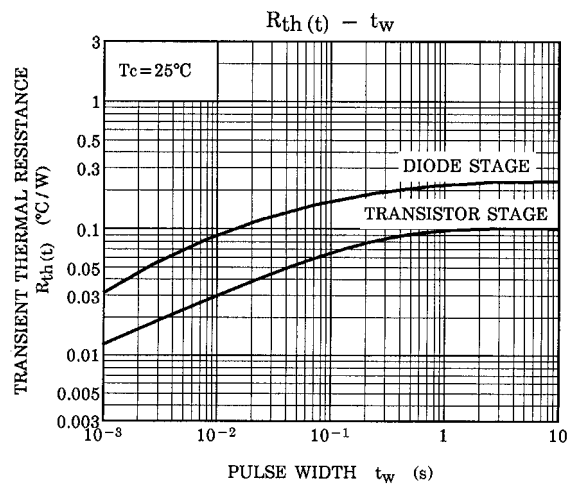
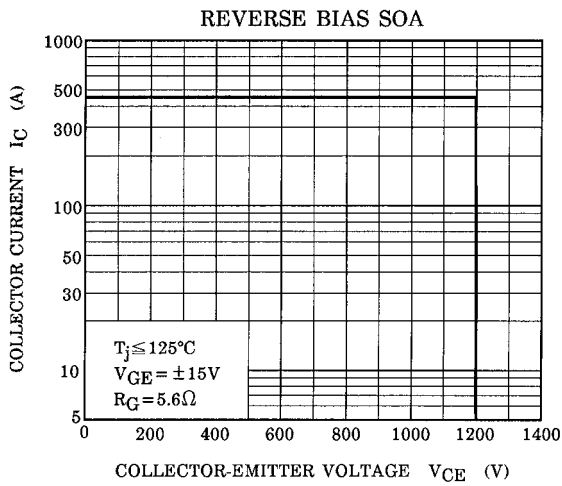
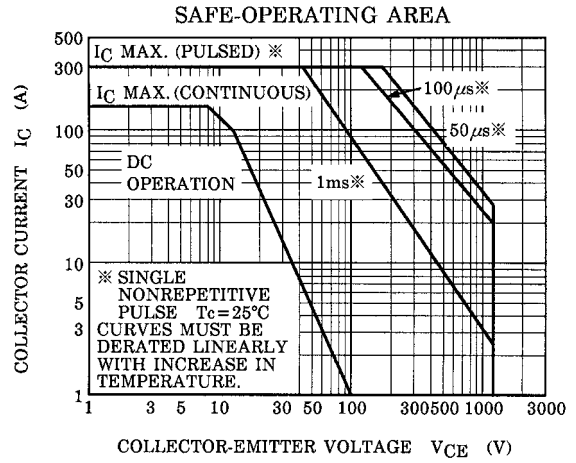
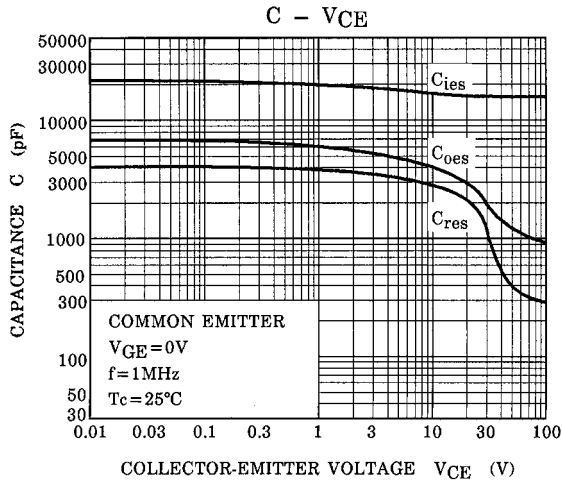
Note 1: Switching time and reverse recovery time test circuit & timing chart











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